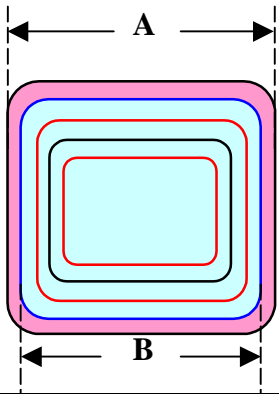


Features : <ul style="list-style-type: none"> * Extremely low forward volts * Guard ring protection * Low reverse leakage current 	Chip size(A):	0.889 * 0.889 mm ²		
	Bond Pad size(B) :	0.762 * 0.762 mm ²		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
Electrical Characteristics		Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C		VF max	0.50	Volt
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C		VR min.	43	Volt.
Minimum Non-repetitive Peak Surge current at 25°C		IFSM	30	Amp
Storage Temperature		TSTG	-65 to +125	°C

HsinChu Headquarter

5F, No. 11, Park Avenue II,
Science-Based Industrial Park,
HsinChu City, Taiwan
TEL: +886-3-567 9979
FAX: +886-3-567 9909

Sales & Marketing

11F, No. 306-3, SEC. 1, Ta Tung Road,
Hsichih, Taipei Hsien 221, Taiwan
TEL: +886-2-8692 1591
FAX: +886-2-8692 1596